



**BSN20** 

### N-CHANNEL ENHANCEMENT MODE FIELD MOSFET

## **Product Summary**

| V <sub>(BR)DSS</sub> | R <sub>DS(ON)</sub>           | I <sub>D</sub><br>T <sub>A</sub> = +25°C |
|----------------------|-------------------------------|--|
| 50V                  | $1.8\Omega @ V_{GS} = 10V$    | 500mA                                    |
|                      | $2.0\Omega$ @ $V_{GS} = 4.5V$ | 450mA                                    |

## **Description**

This new generation MOSFET has been designed to minimize the onstate resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Backlighting
- DC-DC Converters
- **Power Management Functions**

### **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

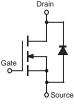
### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208@3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



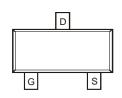
Top View





**Equivalent Circuit** 





Top View

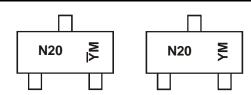
**Ordering Information (Note 5)** 

| Part Number | Qualification | Case  | Packaging        |
|-------------|---------------|-------|------------------|
| BSN20-7     | Standard      | SOT23 | 3000/Tape & Reel |
| BSN20Q-7    | Automotive    | SOT23 | 3000/Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_grade\_definitions/
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



N20 = Product Type Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Y or  $\overline{Y}$  = Year (ex: A = 2013)

M = Month (ex: 9 = September)

Chenadu A/T Site Shanghai A/T Site

| Date Code Key |      |     |      |     |      |     |     |      | _   |      |     |      |
|---------------|------|-----|------|-----|------|-----|-----|------|-----|------|-----|------|
| Year          | 2009 | 9   | 2010 |     | 2011 | 20  | 12  | 2013 |     | 2014 | 2   | 2015 |
| Code          | W    |     | X    |     | Υ    | 2   | 7   | Α    |     | В    |     | С    |
| Month         | Jan  | Feb | Mar  | Apr | May  | Jun | Jul | Aug  | Sep | Oct  | Nov | Dec  |
| Code          | 1    | 2   | 3    | 4   | 5    | 6   | 7   | 8    | 9   | 0    | N   | D    |



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Charac   | teristic          |   | Symbol           | Value      | Units |
|--|-------------------|---|------------------|------------|-------|
| Drain-Source Voltage   |                   |   | V <sub>DSS</sub> | 50         | V     |
| Gate-Source Voltage  |                   |   | V <sub>GSS</sub> | ±20        | V     |
| Continuous Drain Current<br>@ T <sub>SP</sub> = +25°C (Note 6) | Steady<br>State   | $T_A = +25^{\circ}C$<br>$T_A = +100^{\circ}C$ | I <sub>D</sub>   | 500<br>300 | mA    |
| Pulsed Drain Current @ T <sub>SP</sub> = +2                    | 5°C (Notes 6 & 7) | )   | I <sub>DM</sub>  | 1.2        | Α     |

# **Thermal Characteristics**

| Characteristic   | Symbol                            | Value       | Units |
|--|-----------------------------------|-------------|-------|
| Power Dissipation, @T <sub>A</sub> = +25°C (Note 6)                      | P <sub>D</sub>                    | 600         | mW    |
| Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 6) | $R_{	hetaJA}$                     | 200         | °C/W  |
| Power Dissipation, @T <sub>SP</sub> = +25°C (Note 6)                     | $P_{D}$                           | 920         | mW    |
| Thermal Resistance, @T <sub>SP</sub> = +25°C (Note 6)                    | $R_{\theta JSP}$                  | 136         | °C/W  |
| Operating and Storage Temperature Range                                  | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C    |

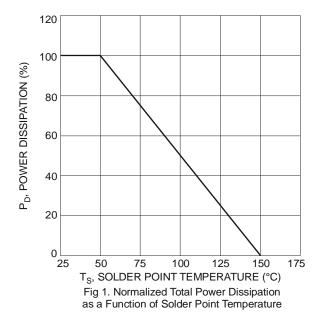
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

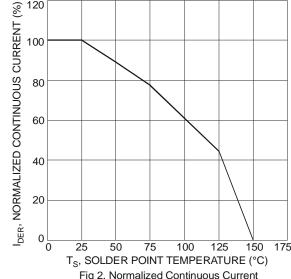
| Characteristic   | Symbol              | Min | Тур        | Max        | Unit | Test Condition   |  |
|--|---------------------|-----|------------|------------|------|--|--|
| OFF CHARACTERISTICS (Note 8)                           |                     |     | - 71       | 1          |      |  |  |
| Drain-Source Breakdown Voltage                         | BV <sub>DSS</sub>   | 50  | -          | _          | V    | $V_{GS} = 0V, I_D = 250\mu A$  |  |
| Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C | I <sub>DSS</sub>    | -   | =          | 0.5        | μA   | V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V                                |  |
| Gate-Body Leakage                                      | I <sub>GSS</sub>    | -   | -          | ±100       | nA   | $V_{GS} = \pm 20V, V_{DS} = 0V$  |  |
| ON CHARACTERISTICS (Note 8)                            |                     |     | •          |            | •    |  |  |
| Gate Threshold Voltage                                 | $V_{GS(th)}$        | 0.4 | 1.0        | 1.5        | V    | $V_{DS} = V_{GS}, I_D = 250 \mu A$   |  |
| Static Drain-Source On-Resistance                      | R <sub>DS(ON)</sub> | -   | 1.3<br>1.6 | 1.8<br>2.0 | Ω    | $V_{GS} = 10V, I_D = 0.22A$<br>$V_{GS} = 4.5V, I_D = 0.1A$                 |  |
| Forward Transfer Admittance                            | Y <sub>fs</sub>     | 40  | 320        | -          | mS   | $V_{DS} = 10V, I_{D} = 0.1A$   |  |
| Diode Forward Voltage                                  | $V_{SD}$            | -   | 1.0        | 1.5        | V    | $V_{GS} = 0V, I_S = 180mA$   |  |
| Source (diode forward) Current                         | Is                  | -   | _          | 194        | mA   | T <sub>SP</sub> = +25°C  |  |
| Peak Source (diode forward) Current                    | I <sub>SM</sub>     | -   | _          | 1.2        | Α    | T <sub>SP</sub> = +25°C (Notes 3 & 4)                                      |  |
| DYNAMIC CHARACTERISTICS (Note 9)                       |                     |     |            |            |      |  |  |
| Input Capacitance                                      | C <sub>iss</sub>    | -   | 21.8       | 40         | pF   |  |  |
| Output Capacitance                                     | Coss                | -   | 5.6        | 15         | pF   | $V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz$                                    |  |
| Reverse Transfer Capacitance                           | C <sub>rss</sub>    | -   | 3.3        | 10         | pF   |  |  |
| Gate Resistance  | $R_g$               | -   | 49         | _          | Ω    | $V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$                                 |  |
| Total Gate Charge                                      | $Q_g$               | -   | 800        | _          | рC   | 101/1/   |  |
| Gate-Source Charge                                     | $Q_{gs}$            | Ī   | 100        | _          | рC   | $V_{GS} = 10V, V_{DD} = 25V,$<br>$V_{DD} = 250 \text{mA}$                  |  |
| Gate-Drain Charge                                      | $Q_{gd}$            | I   | 100        | =          | рC   | - 1D - 230111A   |  |
| Turn-On Delay Time                                     | t <sub>D(on)</sub>  | ī   | 2.93       | _          | ns   | 1/ 201/1/ 101/   |  |
| Turn-On Rise Time                                      | t <sub>r</sub>      |     | 2.99       | =          | ns   | $V_{DD} = 30V, V_{GEN} = 10V,$<br>$R_{I} = 150\Omega, R_{GEN} = 50\Omega,$ |  |
| Turn-Off Delay Time                                    | $t_{D(off)}$        | -   | 9.45       | =          | ns   | $R_L = 15002$ , $R_{GEN} = 5002$ ,<br>$I_D = 0.2A$                         |  |
| Turn-Off Fall Time                                     | t <sub>f</sub>      | _   | 8.3        | _          | ns   |  |  |

Notes:

- 6. Device mounted on FR-4 PCB, with minimum recommended pad layout.
  7. Repetitive rating, pulse width limited by junction temperature.
  8. Short duration pulse test used to minimize self-heating effect.
  9. Guaranteed by design. Not subject to production testing.







120

Fig 2. Normalized Continuous Current vs. Solder Point Temperature

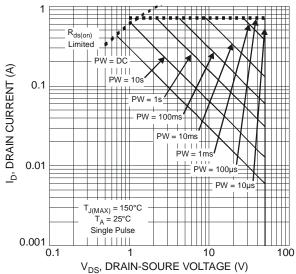


Fig. 3 SOA, Safe Operation Area

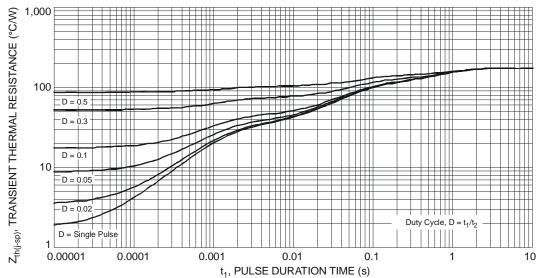
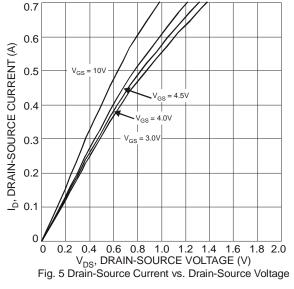
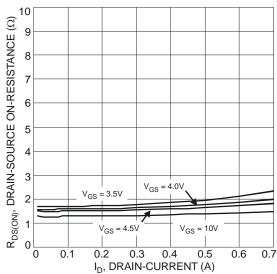
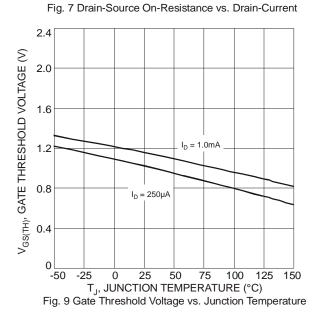


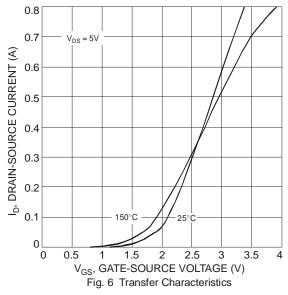
Fig. 4 Transient Thermal Response











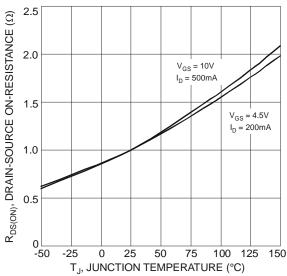
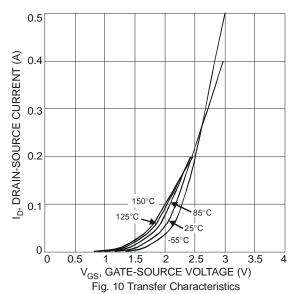
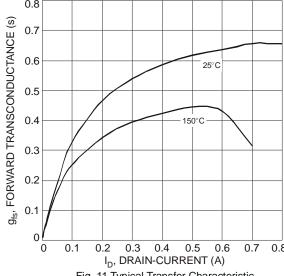
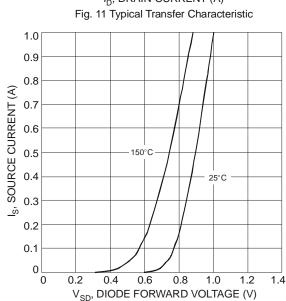


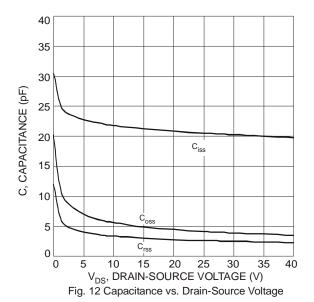
Fig. 8 Drain-Source On-Resistance vs. Junction Temperature







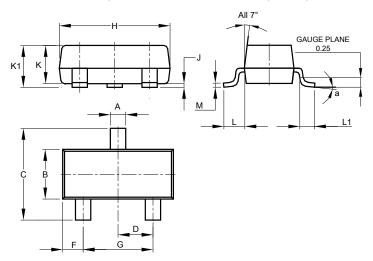




# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

Fig. 13 Source Current vs. Diode Forward Voltage

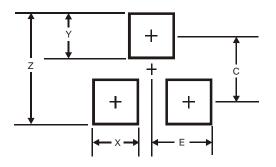


| SOT23 |                      |       |       |  |  |  |  |
|-------|----------------------|-------|-------|--|--|--|--|
| Dim   | Min                  | Max   | Тур   |  |  |  |  |
| Α     | 0.37                 | 0.51  | 0.40  |  |  |  |  |
| В     | 1.20                 | 1.40  | 1.30  |  |  |  |  |
| С     | 2.30                 | 2.50  | 2.40  |  |  |  |  |
| D     | 0.89                 | 1.03  | 0.915 |  |  |  |  |
| F     | 0.45                 | 0.60  | 0.535 |  |  |  |  |
| G     | 1.78                 | 2.05  | 1.83  |  |  |  |  |
| Н     | 2.80                 | 3.00  | 2.90  |  |  |  |  |
| 7     | 0.013                | 0.10  | 0.05  |  |  |  |  |
| K     | 0.890 1.00 0.975     |       |       |  |  |  |  |
| K1    | 0.903                | 1.10  | 1.025 |  |  |  |  |
| L     | 0.45                 | 0.61  | 0.55  |  |  |  |  |
| L1    | 0.25                 | 0.55  | 0.40  |  |  |  |  |
| M     | 0.085                | 0.150 | 0.110 |  |  |  |  |
| α     | 8°                   |       |       |  |  |  |  |
| All   | All Dimensions in mm |       |       |  |  |  |  |



## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| Z          | 2.9           |
| Х          | 0.8           |
| Υ          | 0.9           |
| С          | 2.0           |
| E          | 1.35          |

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